MAX4476AUT Rev. A

RELIABILITY REPORT

FOR

MAX4476AUT

PLASTIC ENCAPSULATED DEVICES

February 13, 2003

MAXIM INTEGRATED PRODUCTS

120 SAN GABRIEL DR.

SUNNYVALE, CA 94086

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Conclusion

The MAX4476 successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards.

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I. Device Description

A. General

The MAX4476 wide-band, low-noise, low-distortion operational amplifier offers Rail-to-Rail® outputs and single-supply operation down to 2.7V. It draws 2.2mA of quiescent supply current per amplifier while featuring ultra-low distortion (0.0002% THD + N), as well as low input voltage-noise density (4.5 nV per root-Hz) and low input current-noise density (0.5fA per root-Hz). These features make the device an ideal choice for applications that require low distortion and/or low noise.

The MAX4476 is unity-gain stable with a gain-bandwidth product of 10MHz. The MAX4476 is available in spacesaving, 6-pin SOT23 packages.

B. Absolute Maximum Ratings

Item

Power-Supply Voltage (VDD to VSS)
Analog Input Voltage (IN_+, IN)
SHDN Input Voltage
Output Short-Circuit Duration to Either Supply
Operating Temperature Range
Junction Temperature
Storage Temperature Range
Lead Temperature (soldering, 10s)
Continuous Power Dissipation (TA = +70°C)
6-pin SOT23
Derates above +70°C
6-pin SOT23

Rating

-0.3V to +6.0V (VSS - 0.3V) to (VDD + 0.3V) (VSS - 0.3V) to +6.0V Continuous -40°C to +125°C +150°C -65°C to +150°C +300°

727mW

9.1mW/°C

II. Manufacturing Information

A. Description/Function:	SOT23, Low-Noise, Low-Distortion, Wide-Band, Rail-to-Rail Op Amp
B. Process:	S12 – Silicon Gate 1.2 micron CMOS
C. Number of Device Transistors:	1095
D. Fabrication Location:	Oregon, USA
E. Assembly Location:	Malaysia, Philippines or Thailand
F. Date of Initial Production:	July, 2001

III. Packaging Information

A. Package Type:	6-Lead SOT23
B. Lead Frame:	Copper
C. Lead Finish:	Solder Plate
D. Die Attach:	N/A
E. Bondwire:	6 mil dia ball
F. Mold Material:	Epoxy with silica filler
G. Bonding Diagram	05-2501-0190
H. Flammability Rating:	Class UL94-V0
I. Classification of Moisture Sensitivity per JEDEC standard JESD22-A112:	Level 1

IV. Die Information

A. Dimensions:	45 x 87 mils
B. Passivation:	Si_3N_4/SiO_2 (Silicon nitride/ Silicon dioxide)
C. Interconnect:	Aluminum
D. Backside Metallization:	None
E. Minimum Metal Width:	1.2 microns (as drawn)
F. Minimum Metal Spacing:	1.2 microns (as drawn)
G. Bondpad Dimensions:	5 mil. Sq.
H. Isolation Dielectric:	SiO ₂
I. Die Separation Method:	Wafer Saw

V. Quality Assurance Information

A. Quality Assurance Contacts:	Jim Pedicord (Reliability Lab Manager Bryan Preeshl (Executive Director of QA)
	Kenneth Huening (Vice President)

- B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet. 0.1% For all Visual Defects.
- C. Observed Outgoing Defect Rate: < 50 ppm
- D. Sampling Plan: Mil-Std-105D

VI. Reliability Evaluation

A. Accelerated Life Test

The results of the 135°C biased (static) life test are shown in **Table 1**. Using these results, the Failure Rate (λ) is calculated as follows:

 $\lambda = \frac{1}{\text{MTTF}} = \frac{4.04}{192 \times 4389 \times 80 \times 2}$ (Chi square value for MTTF upper limit) Temperature Acceleration factor assuming an activation energy of 0.8eV $\lambda = 29.97 \times 10^{-9}$ $\lambda = 29.97 \text{ F.I.T.}$ (60% confidence level @ 25°C)

This low failure rate represents data collected from Maxim's reliability qualification and monitor programs. Maxim also performs weekly Burn-In on samples from production to assure reliability of its processes. The reliability required for lots which receive a burn-in qualification is 59 F.I.T. at a 60% confidence level, which equates to 3 failures in an 80 piece sample. Maxim performs failure analysis on rejects from lots exceeding this level. The attached Burn-In Schematic (Spec. # 06-5736) shows the static circuit used for this test. Maxim also performs 1000 hour life test monitors quarterly for each process. This data is published in the Product Reliability Report (**RR-1M**).

B. Moisture Resistance Tests

Maxim evaluates pressure pot stress from every assembly process during qualification of each new design. Pressure Pot testing must pass a 20% LTPD for acceptance. Additionally, industry standard 85°C/85%RH or HAST tests are performed quarterly per device/package family.

C. E.S.D. and Latch-Up Testing

The OX48-2 die type has been found to have all pins able to withstand a transient pulse of ± 1000 V, per Mil-Std-883 Method 3015 (reference attached ESD Test Circuit). Latch-Up testing has shown that this device withstands a current of ± 250 mA.

Table 1Reliability Evaluation Test Results

MAX4476AUT

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	PACKAGE	SAMPLE SIZE	NUMBER OF FAILURES
Static Life Test	(Note 1)				
	Ta = 135°C Biased Time = 192 hrs.	DC Parameters & functionality		80	1
Moisture Testin	g (Note 2)				
Pressure Pot	Ta = 121°C P = 15 psi. RH= 100% Time = 168hrs.	DC Parameters & functionality	SOT23	77	0
85/85	Ta = 85°C RH = 85% Biased Time = 1000hrs.	DC Parameters & functionality		77	0
Mechanical Stre	ess (Note 2)				
Temperature Cycle	-65°C/150°C 1000 Cycles Method 1010	DC Parameters & functionality		77	0

Note 1: Life Test Data may represent plastic D.I.P. qualification lots.

Note 2: Generic package/process data

Attachment #1

	Terminal A (Each pin individually connected to terminal A with the other floating)	Terminal B (The common combination of all like-named pins connected to terminal B)
1.	All pins except V _{PS1} <u>3/</u>	All V_{PS1} pins
2.	All input and output pins	All other input-output pins

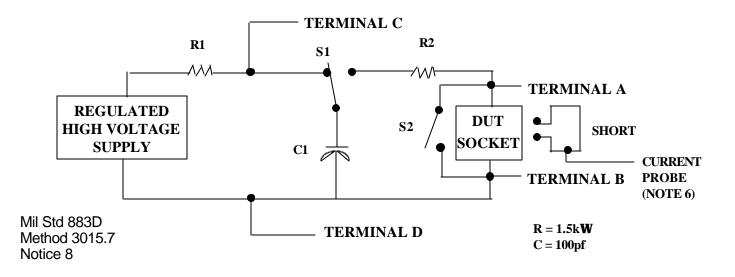
TABLE II. Pin combination to be tested. 1/2/

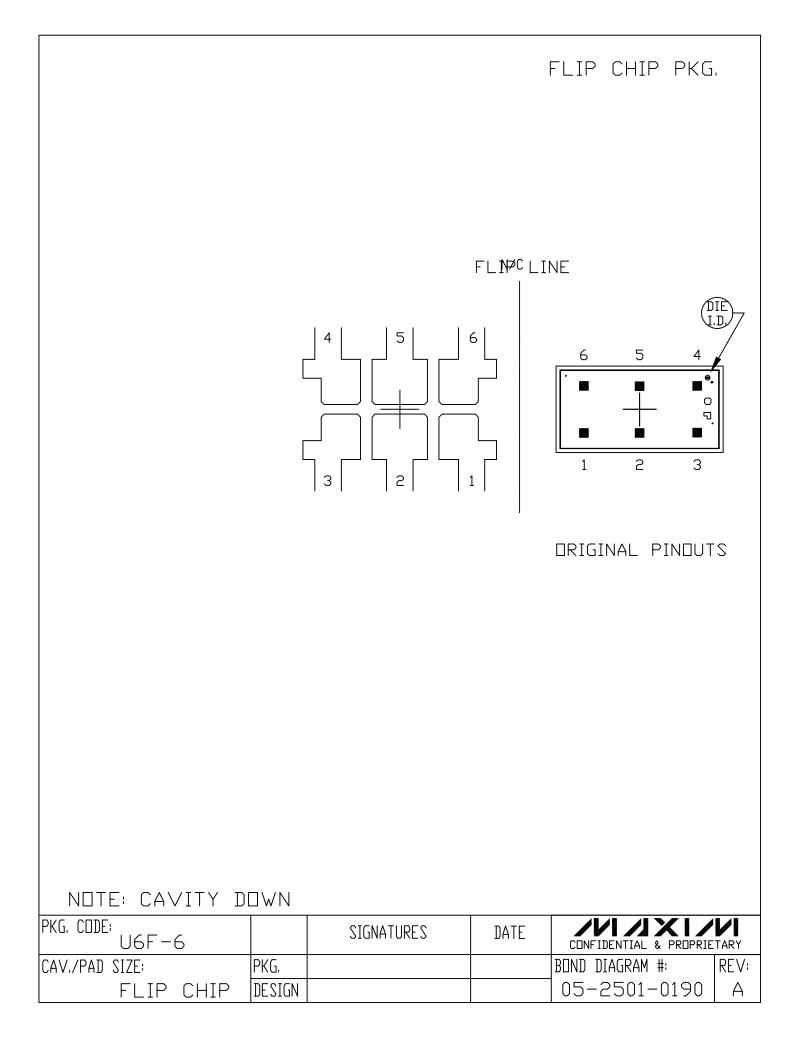
- 1/ Table II is restated in narrative form in 3.4 below.
- $\overline{2/}$ No connects are not to be tested.
- $\overline{3/}$ Repeat pin combination I for each named Power supply and for ground

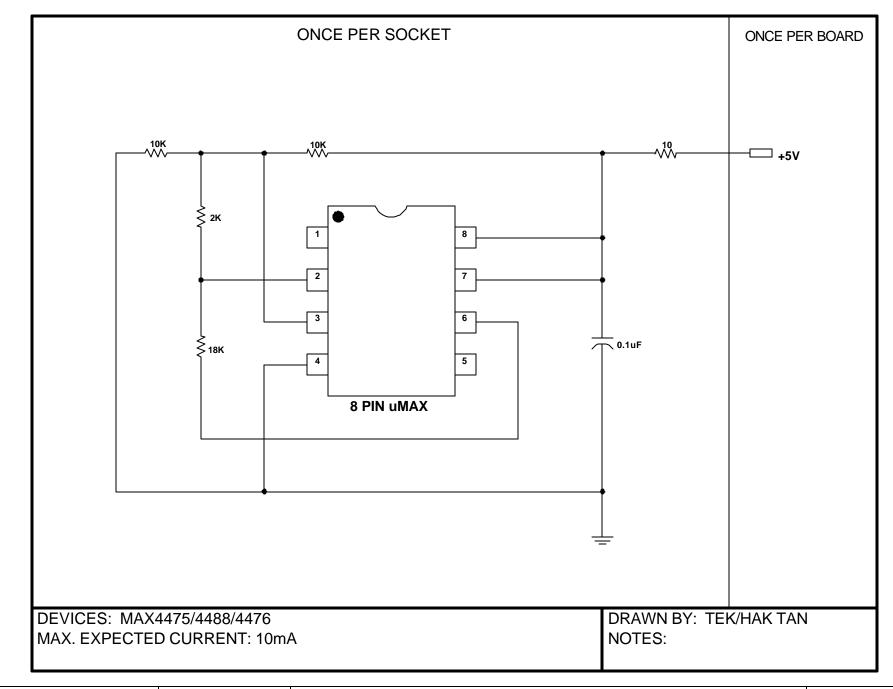
(e.g., where V_{PS1} is V_{DD} , V_{CC} , V_{SS} , V_{BB} , GND, $+V_{S}$, $-V_{S}$, V_{REF} , etc).

- 3.4 <u>Pin combinations to be tested.</u>
 - a. Each pin individually connected to terminal A with respect to the device ground pin(s) connected to terminal B. All pins except the one being tested and the ground pin(s) shall be open.
 - b. Each pin individually connected to terminal A with respect to each different set of a combination of all named power supply pins (e.g., V_{SS1}, or V_{SS2} or V_{SS3} or V_{CC1}, or V_{CC2}) connected to terminal B. All pins except the one being tested and the power supply pin or set of pins shall be open.

c. Each input and each output individually connected to terminal A with respect to a combination of all the other input and output pins connected to terminal B. All pins except the input or output pin being tested and the combination of all the other input and output pins shall be open.







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